WBA0212V 0.5- 1.1 GHz LOW NOISE WIDE BAND AMPLIFIER

Key Features



- 0.5 ~ 1.1 GHz
- 0.60 dB Noise Figure
- 35.0 dBm Output IP₃
- 34.5 dB Gain
- +/-0.30 dB Gain Flatness
- 18.0 dBm P_{1dB}
- 1.25:1 VSWR
- Single Power Supply
- >34 Years MTBF
- Unconditional Stable
- RoHS compliant

Product Description

WBA0212V integrates WanTcom proprietary low noise amplifier technology, high frequency micro electronic assembly techniques, and high reliability design to realize optimum low noise figure, wideband, high linearity, and unconditional stable performances together. With single DC power operation, the amplifier has optimal input and output matching in the specified frequency range at 50-Ohm impedance system. The amplifier has standard SMA connectorized WP-6 gold plated housing.

The amplifier is designed to meet the rugged standard of MIL-STD-202.

Applications

- Mobile Infrastructures
- GPS
- CATV/DBS
- Defense
- Security System
- Measurement
- Fixed Wireless



Specifications

Summary of the electrical specifications WBA0212V at room temperature

Index	Testing Item	Symbol	Test Constraints	Min	Nom	Max	Unit
1	Gain	S ₂₁	0.5 – 1.1 GHz	33.5	34.5	35.5	dB
2	Gain Variation	ΔG	0.5 – 1.1 GHz		+/- 0.3	+/-0.60	dB
3	Input Return Loss	S ₁₁	0.5 – 1.1 GHz	16	20		dB
4	Output VSWR	S ₂₂	0.5 – 1.1 GHz	16	20		dB
5	Reverse Isolation	S ₁₂	0.5 – 1.1 GHz	40	43		dB
6	Noise figure	NF	0.5 – 1.1 GHz		0.60	0.75	dB
7	Output Power 1dB compression Point	P _{1dB}	0.5 – 1.1 GHz	16	18		dBm
8	Output-Third-Order Interception point	IP ₃	Two-Tone, Pout +0 dBm each, 1 MHz separation	32	35		dBm
9	Current Consumption	l _{dd}	V _{dd} = +7 V ~ +35 V		100		mA
10	Power Supply Voltage	V _{dd}		+7		+35	V
11	Thermal Resistance	R _{th,c}	Junction to case, last stage transistor			220	°C/W
12	Operating Temperature	To		-40		+85	°C
13	Maximum Average RF Input Power	PIN, MAX	DC – 6.0 GHz			10	dBm

Absolute Maximum Ratings

Parameters	Units	Ratings
DC Power Supply Voltage	V	35, additional heat sink required
Drain Current	mA	110
Total Power Dissipation	W	3
RF Input Power	dBm	10
Channel Temperature	°C	150
Storage Temperature	°C	-55 ~ 125
Operating Temperature	°C	-40 ~ 85
Thermal Resistance	°C/W	220

Operation of this device above any one of these parameters may cause permanent damage.

Ordering Information

Model Number	WBA0212V	WBA0212VBT
Built-In Bias-T	NO	Yes

Functional Block Diagram



Specifications and information are subject to change without notice.



Typical Data





Small Signal Extended Band Performance @ 25C







Outline, WP-6 Housing

UNITS: INCH [mm] BODY: Brass Finish: Gold Plating RF Connector: SMA F Gold V_{dd} PWR: Feed through



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Application Notes:

A. SMA Torque Wrench Selection

Always use a torque wrench with $5 \sim 6$ inch-lb coupling torque setting for mating the SMA cables to the amplifier. Never use torque more than 8 inch-lb wrench for tightening the mating cable to the connector. Otherwise, the permanent damage will occur to the SMA connectors of the amplifier. 8710-1582 (5 inch-lb) is one of the ideal torque wrench choice from Agilent Technology.

B. DC Power Line Connection

Strip the insulation layer at the end of DC power supply wire. The stripped distance should be in the range of 0.100" to 0.200". The $24 \sim 26$ American Wire Gauge wire is suitable. Wound the stripped terminal wire about 1 to 2 turns on the DC feed thru center pin. Solder the wounded wire and the center pin together. Clean the soldering area by Q-tip with alcohol to remove the flux and residue.

Repeat the process to solder the DC return wire on the ground turret.

C. Mounting the Amplifier

Use three pieces of #4-40 with longer than 9/16" screws for mounting the amplifier on a metal-based chase. Flat and spring washers are needed to prevent the screw loosening during the shock and vibration. Always use the appropriate torque setting of the power screwdriver to mount them.
